Antonino La Magna

List of Publications by Year
in descending order

206	3,552	159585 30	214800 47
papers	citations	h-index	g-index

208	208	208	4174
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Stability of solution-processed MAPbI₃ and FAPbI₃ layers. Physical Chemistry Chemical Physics, 2016, 18, 13413-13422.	2.8	208
2	Temperature-Dependent Optical Band Gap in CsPbBr₃, MAPbBr₃, and FAPbBr₃ Single Crystals. Journal of Physical Chemistry Letters, 2020, 11, 2490-2496.	4.6	173
3	Pb clustering and PbI2 nanofragmentation during methylammonium lead iodide perovskite degradation. Nature Communications, 2019, 10, 2196.	12.8	116
4	Stability and Degradation in Hybrid Perovskites: Is the Glass Half-Empty or Half-Full?. Journal of Physical Chemistry Letters, 2018, 9, 3000-3007.	4.6	102
5	Ambipolar MoS₂ Transistors by Nanoscale Tailoring of Schottky Barrier Using Oxygen Plasma Functionalization. ACS Applied Materials & Interfaces, 2017, 9, 23164-23174.	8.0	81
6	Degradation and hard breakdown transient of thin gate oxides in metalâ€“SiO2â€“Si capacitors: Dependence on oxide thickness. Journal of Applied Physics, 1999, 86, 6382-6391.	2.5	80
7	Similar Structural Dynamics for the Degradation of CH₃NH₃PbI₃ in Air and in Vacuum. ChemPhysChem, 2015, 16, 3064-3071.	2.1	80
8	Delaminated Graphene at Silicon Carbide Facets: Atomic Scale Imaging and Spectroscopy. ACS Nano, 2013, 7, 3045-3052.	14.6	73
9	A phase-field approach to the simulation of the excimer laser annealing process in Si. Journal of Applied Physics, 2004, 95, 4806-4814.	2.5	69
10	Electrical and thermal transient during dielectric breakdown of thin oxides in metal-SiO2-silicon capacitors. Journal of Applied Physics, 1998, 84, 472-479.	2.5	62
11	High-quality 6inch (111) 3C-SiC films grown on off-axis (111) Si substrates. Thin Solid Films, 2010, 518, S165-S169.	1.8	61
12	First Evidence of CH₃NH₃PbI₃ Optical Constants Improvement in a N₂ Environment in the Range 40â€“80 Â°C. Journal of Physical Chemistry C, 2017, 121, 7703-7710.	3.1	49
13	Nitrogen Soaking Promotes Lattice Recovery inÂPolycrystalline Hybrid Perovskites. Advanced Energy Materials, 2019, 9, 1803450.	19.5	46
14	Role of Extended Vacancy-Vacancy Interaction on the Ripening of Voids in Silicon. Physical Review Letters, 1999, 82, 1720-1723.	7.8	45
15	A kinetic Monte Carlo method on super-lattices for the study of the defect formation in the growth of close packed structures. Journal of Computational Physics, 2007, 227, 1075-1093.	3.8	45
16	Role of contact bonding on electronic transport in metalâ€“carbon nanotubeâ€“metal systems. Nanotechnology, 2006, 17, 5063-5072.	2.6	44
17	Chemical Vapor Deposition Growth of Silicon Nanowires with Diameter Smaller Than 5 nm. ACS Omega, 2019, 4, 17967-17971.	3.5	42
18	Extended Defects Formation in Nanosecond Laser-Annealed Ion Implanted Silicon. Nano Letters, 2014, 14, 1769-1775.	9.1	40

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19	Variational study of the discrete Holstein model. Physical Review B, 1996, 53, 8449-8456.	3.2	39
20	Conductance distribution in doped and defected graphene nanoribbons. Physical Review B, 2009, 80, .	3.2	37
21	Molecular doping applied to Si nanowires array based solar cells. Solar Energy Materials and Solar Cells, 2015, 132, 118-122.	6.2	37
22	Revealing a Discontinuity in the Degradation Behavior of CH₃NH₃PbI₃ during Thermal Operation. Journal of Physical Chemistry C, 2017, 121, 13577-13585.	3.1	37
23	Texture of MAPbI₃ Layers Assisted by Chloride on Flat TiO₂ Substrates. Journal of Physical Chemistry C, 2015, 119, 19808-19816.	3.1	36
24	Modeling vacancies and hydrogen impurities in graphene: A molecular point of view. Physics Letters, Section A: General, Atomic and Solid State Physics, 2008, 372, 6168-6174.	2.1	35
25	High-Performance Graphene/AlGaN/GaN Schottky Junctions for Hot Electron Transistors. ACS Applied Electronic Materials, 2019, 1, 2342-2354.	4.3	35
26	Genesis and evolution of extended defects: The role of evolving interface instabilities in cubic SiC. Applied Physics Reviews, 2020, 7, 021402.	11.3	35
27	New Approaches and Understandings in the Growth of Cubic Silicon Carbide. Materials, 2021, 14, 5348.	2.9	34
28	3C-SiC Film Growth on Si Substrates. ECS Transactions, 2011, 35, 99-116.	0.5	32
29	Accelerated Monte Carlo algorithms for defect diffusion and clustering. Computational Materials Science, 2000, 17, 21-33.	3.0	31
30	Local Order and Rotational Dynamics in Mixed A-Cation Lead Iodide Perovskites. Journal of Physical Chemistry Letters, 2020, 11, 1068-1074.	4.6	31
31	Phonon Driven Nonlinear Electrical Behavior in Molecular Devices. Physical Review Letters, 2007, 99, 136404.	7.8	30
32	Mobile intersite bipolarons in the discrete Holstein-Hubbard model. Physical Review B, 1997, 55, 14886-14891.	3.2	29
33	Depth distribution of B implanted in Si after excimer laser irradiation. Applied Physics Letters, 2005, 86, 051909.	3.3	29
34	Defect formation and evolution in the step-flow growth of silicon carbide: A Monte Carlo study. Journal of Crystal Growth, 2008, 310, 971-975.	1.5	29
35	Phase field model of the nanoscale evolution during the explosive crystallization phenomenon. Journal of Applied Physics, 2018, 123, .	2.5	28
36	Atomic transport properties and electrical activation of ultra-low energy implanted boron in crystalline silicon. Materials Science in Semiconductor Processing, 1999, 2, 35-44.	4.0	27

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37	Effect of the miscut direction in (111) 3C-SiC film growth on off-axis (111)Si. Applied Physics Letters, 2009, 94, 101907.	3.3	27
38	Nanostructured TiO₂ Grown by Low-Temperature Reactive Sputtering for Planar Perovskite Solar Cells. ACS Applied Energy Materials, 2019, 2, 6218-6229.	5.1	27
39	From PbI₂ to MAPbI₃ through Layered Intermediates. Journal of Physical Chemistry C, 2016, 120, 19768-19777.	3.1	26
40	CsPbBr₃, MAPbBr₃, and FAPbBr₃ Bromide Perovskite Single Crystals: Interband Critical Points under Dry N₂ and Optical Degradation under Humid Air. Journal of Physical Chemistry C, 2021, 125, 4938-4945.	3.1	26
41	Ion beam induced defects in graphene: Raman spectroscopy and DFT calculations. Journal of Molecular Structure, 2011, 993, 506-509.	3.6	25
42	Impact of Stacking Faults and Domain Boundaries on the Electronic Transport in Cubic Silicon Carbide Probed by Conductive Atomic Force Microscopy. Advanced Electronic Materials, 2020, 6, 1901171.	5.1	25
43	Two-step MAPbI₃ deposition by low-vacuum proximity-space-effusion for high-efficiency inverted semitransparent perovskite solar cells. Journal of Materials Chemistry A, 2021, 9, 16456-16469.	10.3	25
44	Silicon carbide pinch rectifiers using a dual-metal Ti-Ni/sub 2/Si Schottky barrier. IEEE Transactions on Electron Devices, 2003, 50, 1741-1747.	3.0	24
45	Preferential oxidation of stacking faults in epitaxial off-axis (111) 3C-SiC films. Applied Physics Letters, 2009, 95, 111905.	3.3	24
46	Role of the early stages of Ni-Si interaction on the structural properties of the reaction products. Journal of Applied Physics, 2013, 114, .	2.5	24
47	Seedâ€Layerâ€Free Atomic Layer Deposition of Highly Uniform Al₂O₃ Thin Films onto Monolayer Epitaxial Graphene on Silicon Carbide. Advanced Materials Interfaces, 2019, 6, 1900097.	3.7	24
48	Soft breakdown of gate oxides in metalâ€“SiO2â€“Si capacitors under stress with hot electrons. Applied Physics Letters, 1999, 75, 1161-1163.	3.3	23
49	Factors Affecting Profile Evolution in Plasma Etching of SiO[sub 2]. Journal of the Electrochemical Society, 2003, 150, F178.	2.9	23
50	Defect kinetics and dopant activation in submicrosecond laser thermal processes. Applied Physics Letters, 2009, 95, 231901.	3.3	23
51	Material modifications induced by laser annealing in two-dimensional structures. Applied Physics Letters, 2004, 84, 4738-4740.	3.3	22
52	Role of the internal strain on the incomplete Siâ•SiO2 phase separation in substoichiometric silicon oxide films. Applied Physics Letters, 2007, 90, 183101.	3.3	22
53	Extended study of the step-bunching mechanism during the homoepitaxial growth of SiC. Thin Solid Films, 2010, 518, S159-S161.	1.8	22
54	Study of the Anchoring Process of Tethered Unsymmetrical Zn-Phthalocyanines on TiO₂ Nanostructured Thin Films. Journal of Physical Chemistry C, 2013, 117, 11176-11185.	3.1	22

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55	Exploring the orthorhombicâ€“tetragonal phase transition in CH3NH3PbI3: the role of atom kinetics. Nanoscale, 2017, 9, 5896-5903.	5.6	22
56	Electron trapping at SiO₂/4H-SiC interface probed by transient capacitance measurements and atomic resolution chemical analysis. Nanotechnology, 2018, 29, 395702.	2.6	22
57	Diffusion and electrical activation of indium in silicon. Journal of Applied Physics, 2003, 93, 9773-9782.	2.5	21
58	Role of light scattering in excimer laser annealing of Si. Applied Physics Letters, 2005, 86, 161905.	3.3	21
59	Low-Temperature Annealing Combined with Laser Crystallization for Polycrystalline Silicon TFTs on Polymeric Substrate. Journal of the Electrochemical Society, 2008, 155, H764.	2.9	21
60	Energetics and diffusivity of indium-related defects in silicon. Physical Review B, 2004, 69, .	3.2	20
61	Low Stress Heteroepitaxial 3C-SiC Films Characterized by Microstructure Fabrication and Finite Elements Analysis. Journal of the Electrochemical Society, 2010, 157, H438.	2.9	20
62	The ground state of an electron or exciton in the Holstein model. Physics Letters, Section A: General, Atomic and Solid State Physics, 1995, 200, 213-218.	2.1	18
63	Electronic transport in carbon nanotube based nano-devices. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2333-2338.	2.7	17
64	Stacking faults evolution during epitaxial growths: Role of surface the kinetics. Surface Science, 2010, 604, 939-942.	1.9	17
65	Silicon doped by molecular doping technique: Role of the surface layers of doped Si on the electrical characteristics. Materials Science in Semiconductor Processing, 2016, 42, 200-203.	4.0	17
66	Theoretical Monte Carlo Study of the Formation and Evolution of Defects in the Homoepitaxial Growth of SiC. Materials Science Forum, 2008, 600-603, 135-138.	0.3	16
67	Analysis of the role of the particleâ€“wall interaction on the separation efficiencies of field flow fractionation dielectrophoretic devices. Electrophoresis, 2015, 36, 1396-1404.	2.4	16
68	Structural Characterization and Adsorption Properties of Dunino Raw Halloysite Mineral for Dye Removal from Water. Materials, 2021, 14, 3676.	2.9	16
69	The ground state of an extra electron interacting with acoustic phonons in a molecular chain. Physics Letters, Section A: General, Atomic and Solid State Physics, 1995, 205, 90-96.	2.1	15
70	Reduction of thermal damage in ultrathin gate oxides after intrinsic dielectric breakdown. Applied Physics Letters, 2001, 79, 1522-1524.	3.3	15
71	The effect of excimer laser pretreatment on diffusion and activation of boron implanted in silicon. Applied Physics Letters, 2005, 87, 192109.	3.3	15
72	Excimer Laser annealing for shallow junction formation in Si power MOS devices. Thin Solid Films, 2006, 504, 2-6.	1.8	15

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73	Monte Carlo study of the step flow to island nucleation transition for close packed structures. Surface Science, 2009, 603, 2226-2229.	1.9	15
74	Damage Formation and Evolution inÂIon-Implanted Crystalline Si. Topics in Applied Physics, 2009, , 147-212.	0.8	15
75	Substrate and atmosphere influence on oxygen p-doped graphene. Carbon, 2016, 107, 696-704.	10.3	15
76	Structural characterization of Ni2Si pseudoepitaxial transrotational structures on [001] Si. Acta Crystallographica Section B: Structural Science, 2006, 62, 729-736.	1.8	14
77	Bias-driven local density of states alterations and transport in ballistic molecular devices. Journal of Chemical Physics, 2008, 128, 164706.	3.0	14
78	Simultaneous nickel silicidation and silicon crystallization induced by excimer laser annealing on plastic substrate. Applied Physics Letters, 2010, 96, 142113.	3.3	14
79	Crystallization of implanted amorphous silicon during millisecond annealing by infrared laser irradiation. Applied Physics Letters, 2010, 97, .	3.3	14
80	Kinetic Monte Carlo simulations of boron activation in implanted Si under laser thermal annealing. Applied Physics Express, 2014, 7, 021301.	2.4	14
81	TiO₂ Colloids Laser-Treated in Ethanol for Photocatalytic H₂ Production. ACS Applied Nano Materials, 2020, 3, 9127-9140.	5.0	14
82	Generation and Termination of Stacking Faults by Inverted Domain Boundaries in 3C-SiC. Crystal Growth and Design, 2020, 20, 3104-3111.	3.0	14
83	Quasisoliton states in a two-dimensional discrete model. Physical Review B, 1995, 52, 15273-15278.	3.2	13
84	Electrical activation of ultralow energy As implants in Si. Journal of Applied Physics, 2001, 90, 3873-3878.	2.5	13
85	Integration of Melting Excimer Laser Annealing in Power MOS Technology. IEEE Transactions on Electron Devices, 2007, 54, 852-860.	3.0	13
86	Insulator-metal transition in biased finite polyyne systems. European Physical Journal B, 2009, 70, 311-316.	1.5	13
87	Coherent electron transport in quasi one-dimensional carbon-based systems. European Physical Journal B, 2011, 81, 15-36.	1.5	13
88	A comprehensive study on the physicochemical and electrical properties of Si doped with the molecular doping method. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1685-1694.	1.8	13
89	In-situ monitoring by Raman spectroscopy of the thermal doping of graphene and MoS₂ in O₂-controlled atmosphere. Beilstein Journal of Nanotechnology, 2017, 8, 418-424.	2.8	13
90	Role of the indiumâ€“carbon interaction on In diffusion and activation in Si. Applied Physics Letters, 2003, 83, 1956-1958.	3.3	12

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91	Violation of the single-parameter scaling hypothesis in disordered graphene nanoribbons. Physical Review B, 2008, 78, .	3.2	12
92	Pervasive infiltration and multi-branch chemisorption of N-719 molecules into newly designed spongy TiO₂ layers deposited by gig-lox sputtering processes. Journal of Materials Chemistry A, 2017, 5, 25529-25538.	10.3	12
93	3C-SiÐ¡ Hetero-Epitaxially Grown on Silicon Compliance Substrates and New 3C-SiÐ¡ Substrates for Sustainable Wide-Band-Gap Power Devices (CHALLENGE). Materials Science Forum, 2018, 924, 913-918.	0.3	12
94	3C-SiC Growth on Inverted Silicon Pyramids Patterned Substrate. Materials, 2019, 12, 3407.	2.9	12
95	Ni/4H-SiC interaction and silicide formation under excimer laser annealing for ohmic contact. Materialia, 2020, 9, 100528.	2.7	12
96	Exploring the Structural Competition between the Black and the Yellow Phase of CsPbI3. Nanomaterials, 2021, 11, 1282.	4.1	12
97	Ni Schottky barrier on heavily doped phosphorous implanted 4H-SiC. Journal Physics D: Applied Physics, 2021, 54, 445107.	2.8	12
98	One particle interacting with the acoustical phonons in a discrete chain. Physical Review B, 1997, 55, 6296-6303.	3.2	11
99	Computational analysis of etched profile evolution for the derivation of 2D dopant density maps in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 102, 43-48.	3.5	11
100	Electrical activation phenomena induced by excimer laser annealingin B-implanted silicon. Applied Physics Letters, 2004, 85, 2268-2270.	3.3	11
101	Nucleation and growth of NiSi from Ni2Si transrotational domains. Applied Physics Letters, 2007, 90, 053507.	3.3	10
102	Ab InitioStudy of Ge Intercalation in Epitaxial Graphene on SiC(0001). Applied Physics Express, 2011, 4, 125101.	2.4	10
103	Nanofabrication processes for innovative nanohole-based solar cells. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1564-1570.	1.8	10
104	Transparent conductive polymer obtained by in-solution doping of PEDOT:PSS. Polymer, 2018, 155, 199-207.	3.8	10
105	Direct observation of single organic molecules grafted on the surface of a silicon nanowire. Scientific Reports, 2019, 9, 5647.	3.3	10
106	Multiscale modeling of ultrafast melting phenomena. Npj Computational Materials, 2022, 8, .	8.7	10
107	Enhanced boron diffusion in excimer laser preannealed Si. Applied Physics Letters, 2005, 86, 151902.	3.3	9
108	A mean field approach to many-particles effects in dielectrophoresis. Applied Physics Letters, 2008, 93, 193902.	3.3	9

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109	Study of the connection between stacking faults evolution and step kinetics in misoriented 4H-SiC epitaxial growths. Surface Science, 2011, 605, L67-L69.	1.9	9
110	A numerical method for the efficient atomistic simulation of the plasma-etch of nano-patterned structures. Computational Materials Science, 2012, 54, 227-235.	3.0	9
111	Controlled Al3+ Incorporation in the ZnO Lattice at 188 Â°C by Soft Reactive Co-Sputtering for Transparent Conductive Oxides. Energies, 2016, 9, 433.	3.1	9
112	High aspect ratio tilted gratings through local electric field modulation in plasma etching. Applied Surface Science, 2022, 588, 152938.	6.1	9
113	Outâ€ofâ€Glovebox Integration of Recyclable Europiumâ€Doped CsPbI₃ in Tripleâ€Mesoscopic Carbonâ€Based Solar Cells Exceeding 9% Efficiency. Solar Rrl, 2022, 6, .	5.8	9
114	Nanoisland shape relaxation mechanism. Surface Science, 2007, 601, 308-314.	1.9	8
115	Boron Electrical Activation in Crystalline Si after Millisecond Nonmelting Laser Irradiation. Journal of the Electrochemical Society, 2008, 155, H603.	2.9	8
116	Theoretical study of the role of metallic contacts in probing transport features of pure and defected graphene nanoribbons. Nanoscale Research Letters, 2011, 6, 234.	5.7	8
117	Study of the Effects of Growth Rate, Miscut Direction and Postgrowth Argon Annealing on the Surface Morphology of Homoepitaxially Grown 4H Silicon Carbide Films. Materials Science Forum, 0, 740-742, 229-234.	0.3	8
118	Nitrogen doped spongy TiO2 layers for sensors application. Materials Science in Semiconductor Processing, 2019, 98, 44-48.	4.0	8
119	Full Efficiency Recovery in Hole-Transporting Layer-Free Perovskite Solar Cells With Free-Standing Dry-Carbon Top-Contacts. Frontiers in Chemistry, 2020, 8, 200.	3.6	8
120	Formation of CsPbI₃ Î³â€Phase at 80â€‰Â°C by Europiumâ€Assisted Snowplow Effect. Advanced Energy and Sustainability Research, 2021, 2, 2100091.	5.8	8
121	Blackâ€Yellow Bandgap Tradeâ€Off During Thermal Stability Tests in Lowâ€Temperature Euâ€Doped CsPbI₃. Solar Rrl, 2022, 6, .	5.8	8
122	Schottky Barrier Inhomogeneities in Nickel Silicide Transrotational Contacts. Applied Physics Express, 2011, 4, 115701.	2.4	7
123	Study of microstructure deflections and film/substrate curvature under generalized stress fields and mechanical properties. Thin Solid Films, 2012, 522, 26-29.	1.8	7
124	Analysis of the role of elution buffers on the separation capabilities of dielectrophoretic devices. Sensing and Bio-Sensing Research, 2016, 7, 162-167.	4.2	7
125	Bimodal Porosity and Stability of a TiO2 Gig-Lox Sponge Infiltrated with Methyl-Ammonium Lead Iodide Perovskite. Nanomaterials, 2019, 9, 1300.	4.1	7
126	Study on the Physico-Chemical Properties of the Si Nanowires Surface. Nanomaterials, 2019, 9, 818.	4.1	7

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127	Surface segregated Ga, In, and Al activation in high Ge content SiGe during UV melt laser induced non-equilibrium solidification. Japanese Journal of Applied Physics, 2019, 58, 120911.	1.5	7
128	Improved Electrical and Structural Stability in HTL-Free Perovskite Solar Cells by Vacuum Curing Treatment. Energies, 2020, 13, 3953.	3.1	7
129	Inter-diffusion, melting and reaction interplay in Ni/4H-SiC under excimer laser annealing. Applied Surface Science, 2021, 539, 148218.	6.1	7
130	Atomic scale computer aided design for novel semiconductor devices. Computational Materials Science, 2003, 27, 10-15.	3.0	6
131	Nonequilibrium electron charging in carbon-nanotube-based molecular bridges. Applied Physics Letters, 2007, 91, 163111.	3.3	6
132	Defect and dopant kinetics in laser anneals of Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 154-155, 35-38.	3.5	6
133	Atomistic and Continuum Simulations of the Homo-Epitaxial Growth of SiC. Materials Science Forum, 0, 615-617, 73-76.	0.3	6
134	Stress nature investigation on heteroepitaxial 3Câ€“SiC film on (100) Si substrates. Journal of Materials Research, 2013, 28, 129-135.	2.6	6
135	Ultrafast Generation of Unconventional<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mo stretchy="false">{</mml:mo><mml:mn>001</mml:mn><mml:mo stretchy="false">}</mml:mo></mml:mrow></mml:math>Loops in Si. Physical Review Letters, 2017, 119, 205503.	7.8	6
136	Multi-objective optimization and analysis for the design space exploration of analog circuits and solar cells. Engineering Applications of Artificial Intelligence, 2017, 62, 373-383.	8.1	6
137	Simulation of the Growth Kinetics in Group IV Compound Semiconductors. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1800597.	1.8	6
138	Optical behaviour of Î³-black CsPbI₃ phases formed by quenching from 80 Â°C and 325 Â°C. JPhys Materials, 2021, 4, 034011.	4.2	6
139	Simulations of the Ultra-Fast Kinetics in Ni-Si-C Ternary Systems under Laser Irradiation. Materials, 2021, 14, 4769.	2.9	6
140	Surface, stress, and impurity effects on room-temperature migration of ion-beam-generated point defects. Applied Physics Letters, 1998, 73, 1571-1573.	3.3	5
141	Point defect diffusion and clustering in ion implanted c-Si. Nuclear Instruments & Methods in Physics Research B, 2001, 178, 25-32.	1.4	5
142	Correlation between macroscopic and microscopic stress fields: Application to the 3Câ€“SiC/Si heteroepitaxy. Journal of Materials Research, 2013, 28, 104-112.	2.6	5
143	High Resolution Investigation of Stacking Fault Density by HRXRD and STEM. Materials Science Forum, 0, 963, 346-349.	0.3	5
144	Extensive Fermiâ€Level Engineering for Graphene through the Interaction with Aluminum Nitrides and Oxides. Physica Status Solidi - Rapid Research Letters, 2020, 14, 1900399.	2.4	5

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145	Phononic transport and simulations of annealing processes in nanometric complex structures. Physical Review Materials, 2020, 4, .	2.4	5
146	Topographic and structural evolution of etched Si samples. Computational Materials Science, 2002, 24, 246-251.	3.0	4
147	Room temperature defect diffusion in ion implanted c-Si. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 265-270.	1.4	4
148	A polaron model of the electronic transport in a nanotube quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2289-2293.	2.7	4
149	Process simulation of hydrogen intercalation in epitaxial graphene on SiC(0001). Physica Status Solidi (B): Basic Research, 2013, 250, 1478-1482.	1.5	4
150	Porous Gig-Lox TiO2 Doped with N2 at Room Temperature for P-Type Response to Ethanol. Chemosensors, 2019, 7, 12.	3.6	4
151	Design and characterization of effective solar cells. Energy Systems, 2022, 13, 355-382.	3.0	4
152	Notching Effect on Metal Etch: A Very Simple Predictive Model. IEEE Transactions on Semiconductor Manufacturing, 2005, 18, 355-358.	1.7	3
153	Electron transport properties of calix[4]arene based systems in a metalâ€“moleculeâ€“metal junction. New Journal of Chemistry, 2007, 31, 756-761.	2.8	3
154	Multiscale simulation for epitaxial silicon carbide growth by chlorides route. Thin Solid Films, 2010, 518, S6-S11.	1.8	3
155	Strain Field Analysis of 3C-SiC Free-Standing Microstructures by Micro-Raman and Theoretical Modelling. Materials Science Forum, 2012, 711, 55-60.	0.3	3
156	Effects of the Growth Rate on the Quality of 4H Silicon Carbide Films for MOSFET Applications. Materials Science Forum, 0, 778-780, 95-98.	0.3	3
157	Fluorocarbon Chemistry: A 0-Dimensional Model for Oxide and Nitride Dry Etching. IEEE Transactions on Semiconductor Manufacturing, 2015, 28, 337-344.	1.7	3
158	Enhancing quantum efficiency of thin-film silicon solar cells by Pareto optimality. Journal of Global Optimization, 2018, 72, 491-515.	1.8	3
159	Surface Plasmons in Silicon Nanowires. Advanced Photonics Research, 2021, 2, 2100130.	3.6	3
160	From Point to Extended Defects in Silicon: A Theoretical Study. Solid State Phenomena, 2001, 85-86, 177-202.	0.3	2
161	Atomistic simulations and the requirements of process simulator for novel semiconductor devices. Computational Materials Science, 2002, 24, 213-222.	3.0	2
162	Quantitative Measurements of Two-Dimensional Ultrashallow B Profiles in Si by Selective Chemical Etching. Journal of the Electrochemical Society, 2005, 152, G277.	2.9	2

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163	Ultra-shallow junction by laser annealing: Integration issues and modelling. Nuclear Instruments & Methods in Physics Research B, 2006, 253, 1-8.	1.4	2
164	Effects of interface bonding on the conductance of metalâ€“carbon nanotubeâ€“metal systems. Materials Science and Engineering C, 2007, 27, 1102-1107.	7.3	2
165	Study of the Impact of Growth and Post-Growth Processes on the Surface Morphology of 4H Silicon Carbide Films. Materials Science Forum, 2012, 717-720, 149-152.	0.3	2
166	Monte Carlo Study of the Early Growth Stages of 3C-SiC on Misoriented and 6H-Sic Substrates. Materials Science Forum, 2014, 778-780, 238-242.	0.3	2
167	Atomic scale Monte Carlo simulations of BF₃ plasma immersion ion implantation in Si. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 109-112.	0.8	2
168	Role of the early stages of Ni-Si interaction on the formation of transrotational Ni-silicides. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 164-168.	0.8	2
169	Monte Carlo Study of the early Growth Stages of 3C-SiC on Misoriented <11-20> and <1-100> 6H-SiC Substrates: Role of Step-Island Interaction. Materials Science Forum, 2015, 821-823, 201-204.	0.3	2
170	Atom by Atom Simulations of Nanomaterial Manipulation: The Plasma Etching Case. IEEE Nanotechnology Magazine, 2017, 16, 790-797.	2.0	2
171	Advanced simulations on laser annealing: explosive crystallization and phonon transport corrections. , 2020, , .		2
172	Structural and Electrical Characterization of Ni-Based Ohmic Contacts on 4H-SiC Formed by Solid-State Laser Annealing. Materials Science Forum, 0, 1062, 417-421.	0.3	2
173	Self-Interstitial Kinetics and Transient Phenomena in Si Crystals. Solid State Phenomena, 2001, 82-84, 171-176.	0.3	1
174	Low Power Dissipation SiC Schottky Rectifiers with a Dual-Metal Planar Structure. Materials Science Forum, 2003, 433-436, 819-822.	0.3	1
175	Role of the Siâ•SiO2 interface during dopant diffusion in thin silicon on insulator layers. Journal of Applied Physics, 2006, 100, 096112.	2.5	1
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